

Features

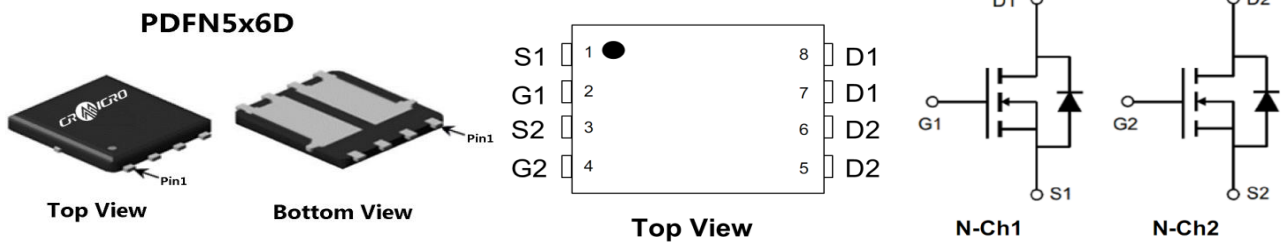
- Uses CRM(CQ) advanced Trench technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)

Applications

- Motor drive

Product Summary

Symbol	N-Ch1	N-Ch2
V_{DS}	60V	60V
$R_{DS(on)}$ typ.	11m Ω	11m Ω
I_D	27A	27A

100% DVDS Tested
100% Avalanche Tested

Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRMP110N06L2S	M060BS06	PDFN5x6D	Taping	N/A	N/A	4000pcs

Absolute Maximum Ratings

Parameter	Symbol	Maximum		Unit
		N-Ch1	N-Ch2	
Drain-source voltage	V_{DS}	60	60	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit)	I_D	69	69	A
Continuous drain current $T_C = 25^\circ\text{C}$ (Package limit)	I_D	27.0	27.0	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D\ pulse}$	108	108	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	E_{AS}	135	135	mJ
Gate-Source voltage	V_{GS}	± 20	± 20	V
Power dissipation ($T_A = 25^\circ\text{C}$) ¹	P_{tot}	2	2	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150		$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Typ	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	1.3	1.8	°C/W
SMD version, device on PCB ² Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	58.0	69.6	°C/W

NOTE:

 1.The power dissipation PD is based on $T_{j(MAX)}=150^{\circ}C$, using $\leq 10s$ junction-to-ambient thermal resistance.

 2.The value of R_{thJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The value in any given application depends on the user's specific board design.

N-Ch1&N-Ch2 Electrical Characteristic (at $T_j = 25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

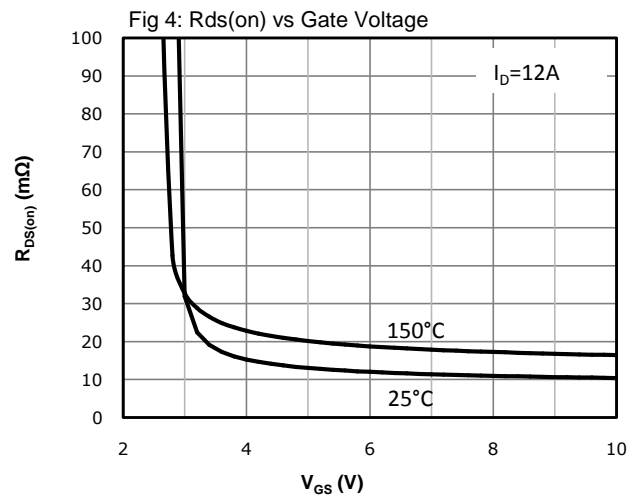
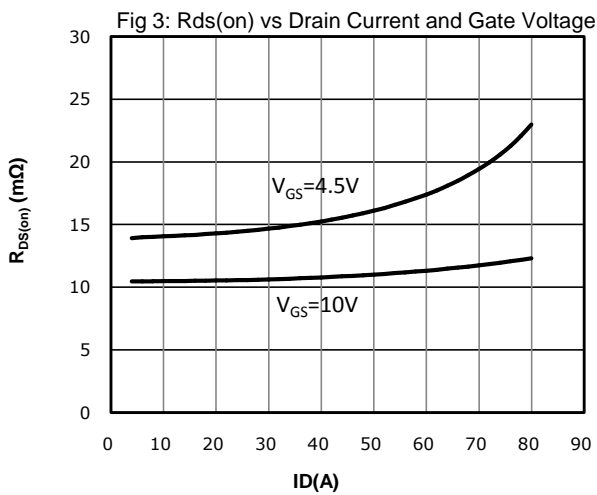
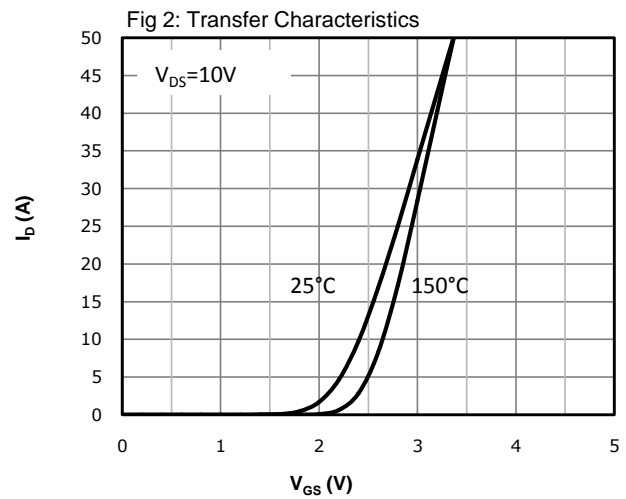
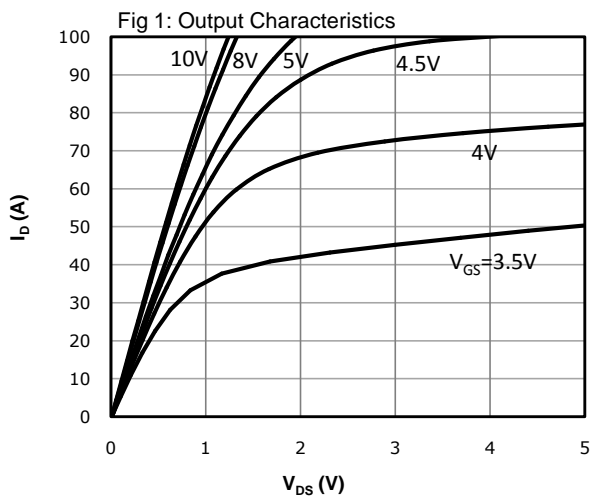
Drain-source breakdown voltage	BV_{DSS}	60	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	1	1.6	2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.08	1	μA	$V_{DS}=60V, V_{GS}=0V$ $T_j=25^{\circ}C$ $T_j=125^{\circ}C$
Gate-source leakage current	I_{GSS}	-	± 10	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	14.0	16.8	m Ω	$V_{GS}=4.5V, I_D=10A$ $V_{GS}=10V, I_D=10A$
Transconductance	g_{fs}	-	54	-	S	$V_{DS}=5V, I_D=12A$

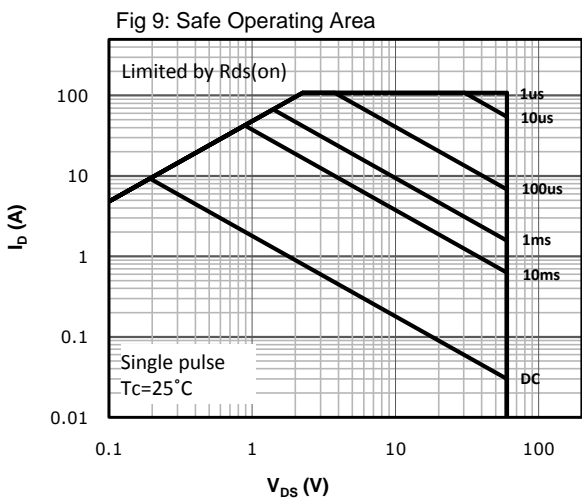
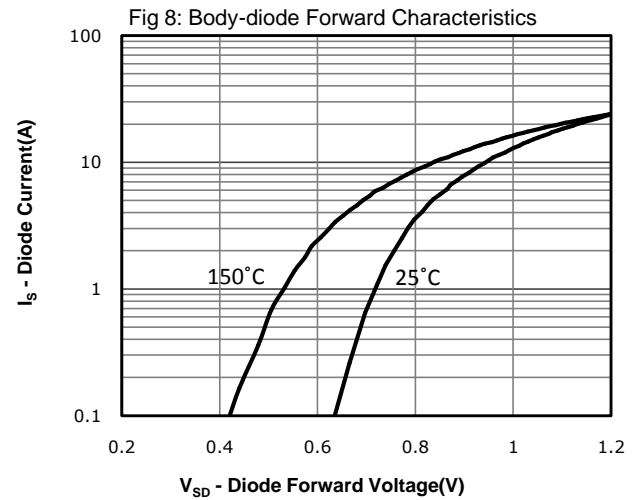
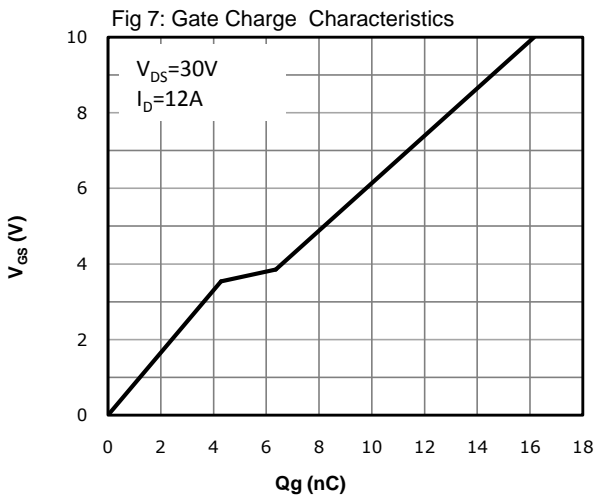
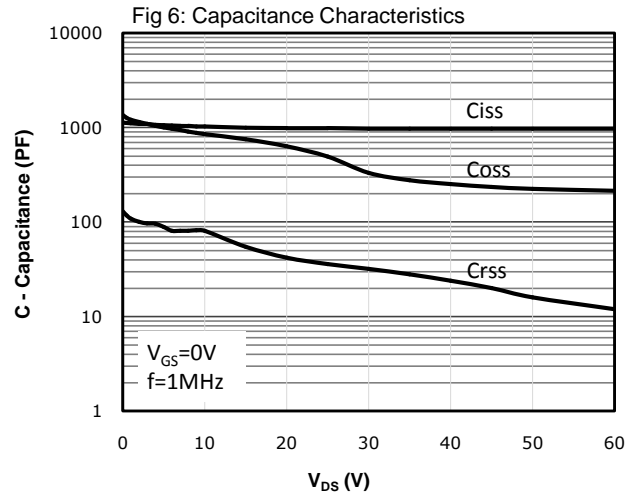
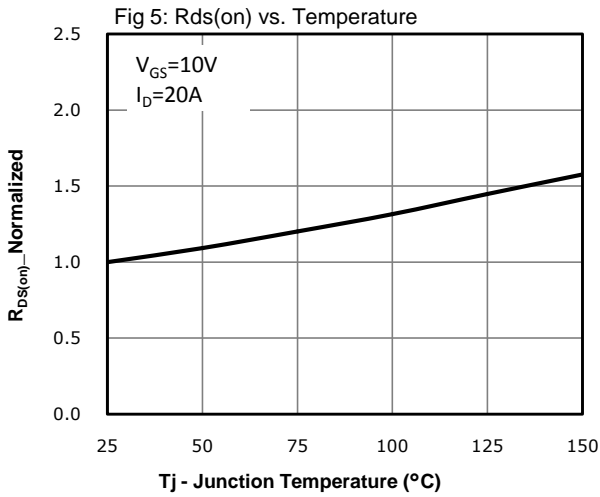
Dynamic Characteristic

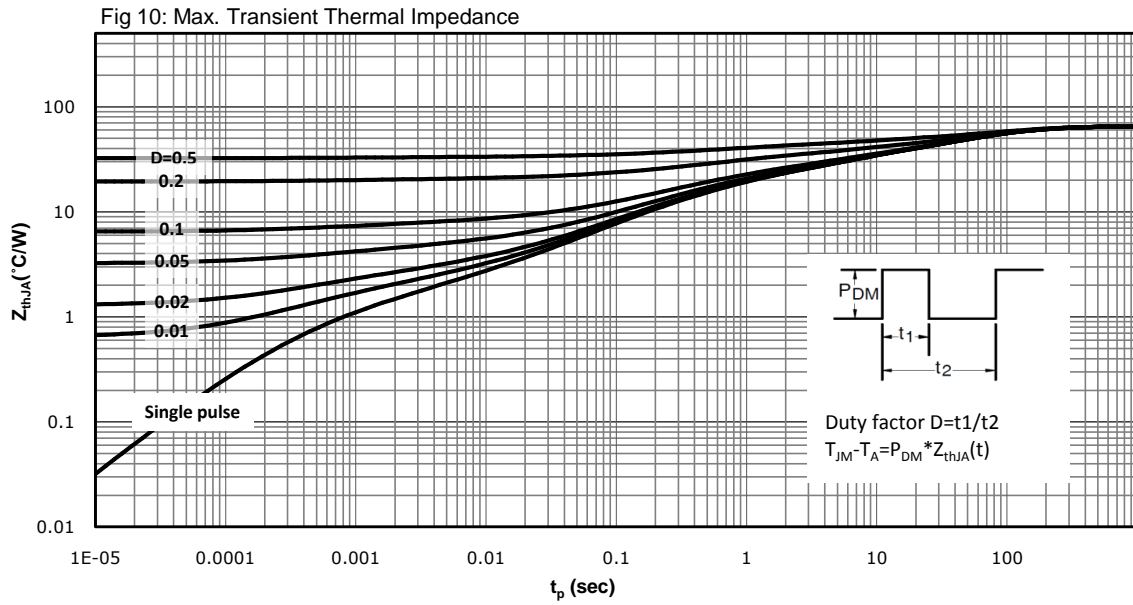
Input Capacitance	C_{iss}	-	972	-	pF	$V_{GS}=0V, V_{DS}=30V, f=1MHz$
Output Capacitance	C_{oss}	-	325	-		
Reverse Transfer Capacitance	C_{rss}	-	31	-		
Gate Total Charge	Q_G	-	16	-	nC	$V_{GS}=10V, V_{DS}=30V, I_D=12A, f=1MHz$
Gate-Source charge	Q_{gs}	-	4.1	-		
Gate-Drain charge	Q_{gd}	-	2.1	-		
Turn-on delay time	$t_{d(on)}$	-	7.9	-	ns	$V_{GS}=10V, V_{DD}=30V, R_{G_ext}=2.7\Omega, I_D=12A$
Rise time	t_r	-	35.1	-		
Turn-off delay time	$t_{d(off)}$	-	19.1	-		
Fall time	t_f	-	38.5	-		
Gate resistance	R_G	-	2.0	-	Ω	$V_{GS}=0V, V_{DS}=0V, f=1MHz$

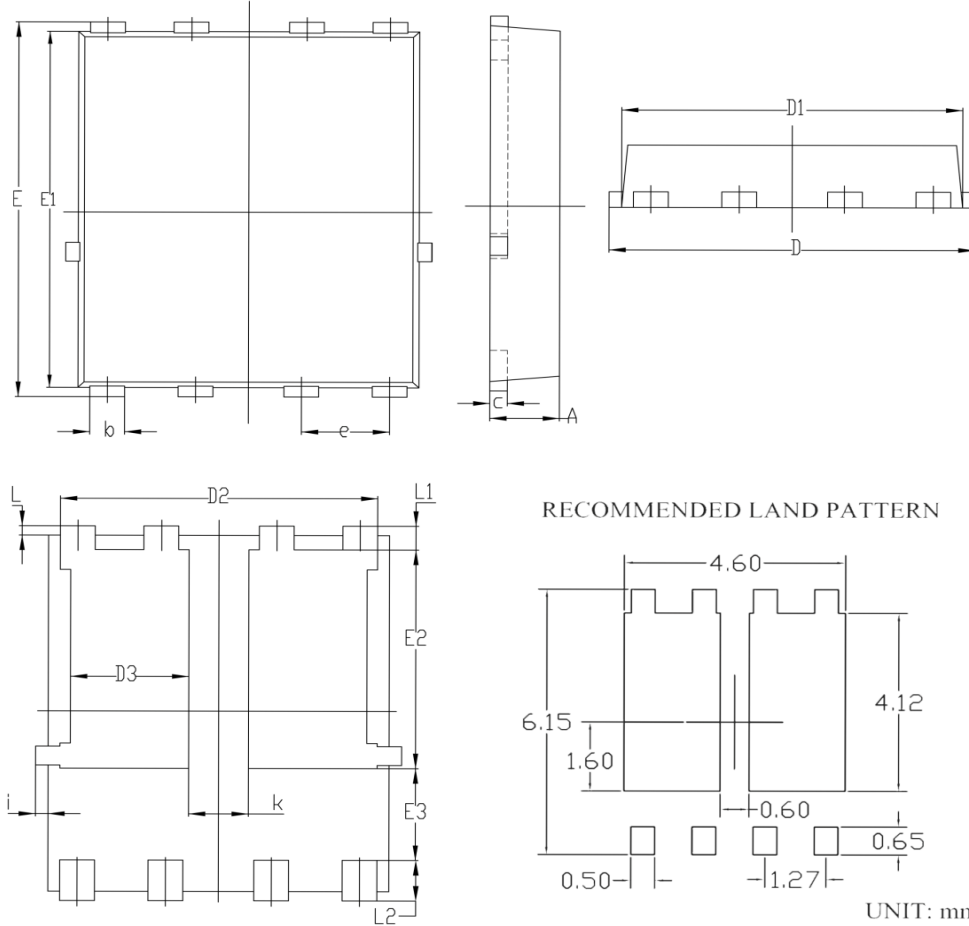
Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.99	1.2	V	$V_{GS}=0V, I_{SD}=12A$
Body Diode Reverse Recovery Time	t_{rr}	-	119.7	-	ns	$I_F=12A, dI/dt=300A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	420.5	-	nC	

N-Ch1&N-Ch2 Typical Performance Characteristics






Package Outline: PDFN5x6D


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.15	0.035	0.039	0.045
b	0.25	0.39	0.52	0.010	0.015	0.020
c	0.20	0.25	0.30	0.008	0.010	0.012
D	4.80	5.10	5.40	0.189	0.201	0.213
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.90	4.20	4.50	0.154	0.165	0.177
D3	1.50	1.70	1.90	0.059	0.067	0.075
E	5.90	6.05	6.20	0.232	0.238	0.244
E1	5.45	5.70	5.85	0.215	0.224	0.230
E2	3.30	3.50	3.80	0.130	0.138	0.150
E3	1.10	----	----	0.043	----	----
e	1.27 BSC			0.050 BSC		
L	0.05	0.15	0.25	0.002	0.006	0.010
L1	0.38	----	0.75	0.015	----	0.030
L2	0.38	----	0.75	0.015	----	0.030
i	----	----	0.18	----	----	0.007
k	0.50	----	----	0.020	----	----

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

Revision History

Revision	Date	Major changes
3.1	2022/12/13	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

单击下面可查看定价，库存，交付和生命周期等信息

[>>CRMICRO\(华润微\)](#)